

In the Specification:

Amend the paragraph between page 9, line 24 to page 10, line 12 as follows:

Exemplary ranges for the energy, flux, and pulse duration of the particles 6 applied to anneal the region 2 are as follows. The energy of the charged particles [[4]] 6 can range from one-tenth (0.1) to one-hundred (100) kilo-electronVolts, the most preferred range being from five (5) to seven (7) keV for electrons. The charged particle dose generally ranges from 10^{12} to 10^{18} particles per square centimeter at the surface 3 of the substrate 1. Determination of the pulse duration of the particle irradiation [[4]] 6 to be applied to the region 2 should utilize the following considerations. In general, it is desirable to heat the region 2 uniformly from surface 3 to lower surface 5 of the dopant profile. The pulse duration should also be sufficiently limited so that minimal dopant diffusion occurs and so that the thermal diffusion length is limited to the desired annealing depth or by practical limitations of the equipment. This minimizes the power required to anneal the region. In general, the pulse duration can be from 10^{-9} to 10^{-4} seconds. However, commercially-available implantation equipment limits the pulse duration to a range from about 5×10^{-7} to 10^{-4} seconds. With implantation equipment currently available greater implant voltages and longer pulse times than the most preferred pulse duration are required. Nonetheless, effective annealing can be performed with the limitations of commercially-available equipment.